WHAT IS CLAIMED IS:

1. A near field light generating device, comprising:

a light emitting element that emits light from its exit surface; and

a thin film that is formed on the exit surface and gains a light transmitting property when irradiated with light from said light emitting element.

2. A near field light generating device according to Claim 1, wherein said thin film changes its state from crystalline to amorphous when irradiated with light from said light emitting element.

3. A near field light generating device according to Claim 1, wherein said thin film returns to a crystalline state from an amorphous state when the light emission is stopped.

4. A near field light generating device according to Claim 1, wherein said thin film essentially consists of inorganic material having a melting point of 350℃ or lower.

5. A near field light generating device according to Claim 1, wherein said thin film essentially consists of inorganic material having a melting point of 150℃ or lower.

6. A near field light generating device according to Claim 1, wherein said thin film essentially consists of organic material having a low melting point.

7. A near field light generating device according to Claim 1, further comprising a heat diffusion preventing film between the light exit surface and the thin film.

8. A near field light generating device according to Claim 1, wherein said light emitting element includes semiconductor laser device.

9. A near field light generating device, comprising:

a light emitting element that emits light from its exit surface; and

a thin film that is formed on the exit surface and gains a light transmitting property when heated.

10. A near field light generating device according to Claim 9, wherein said thin film changes its state from crystalline to amorphous when heated.

11. A near field light generating device according to Claim 9, wherein said thin film returns to a crystalline state from an amorphous state when the heating is stopped.

12. A near field light generating device according to Claim 9, wherein said thin film essentially consists of inorganic material having a melting point of 350°C or lower.

13. A near field light generating device according to Claim 9, wherein said thin film essentially consists of inorganic material having a melting point of 150°C or lower.

14. A near field light generating device according to Claim 9, wherein said thin film essentially consists of organic material having a low melting point.

15. A near field light generating device according to Claim 9, further comprising a heat diffusion preventing film between the light exit surface and the thin film

16. A near field light generating device according to Claim 9, wherein said light emitting element includes semiconductor laser device.

17. A near field light generating device according to Claim 9, wherein said thin film is heated by the light emitted from said light emitting element.